

SOT-363 Plastic-Encapsulate Transistors

UMX1N DUAL TRANSISTOR (NPN+NPN)

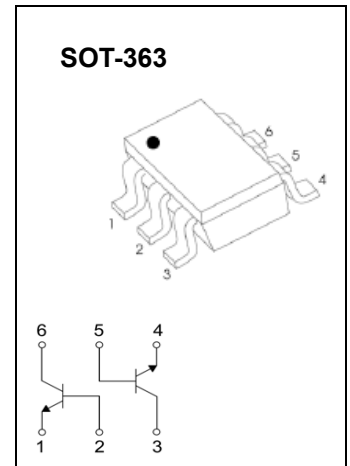
FEATURES

- Two 2SC2412K chips in a SOT-363 package
- Mounting possible with SOT-363 automatic mounting machines
- Transistor elements are independent, eliminating interference
- Mounting cost and area can be cut in half

MARKING:X1

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

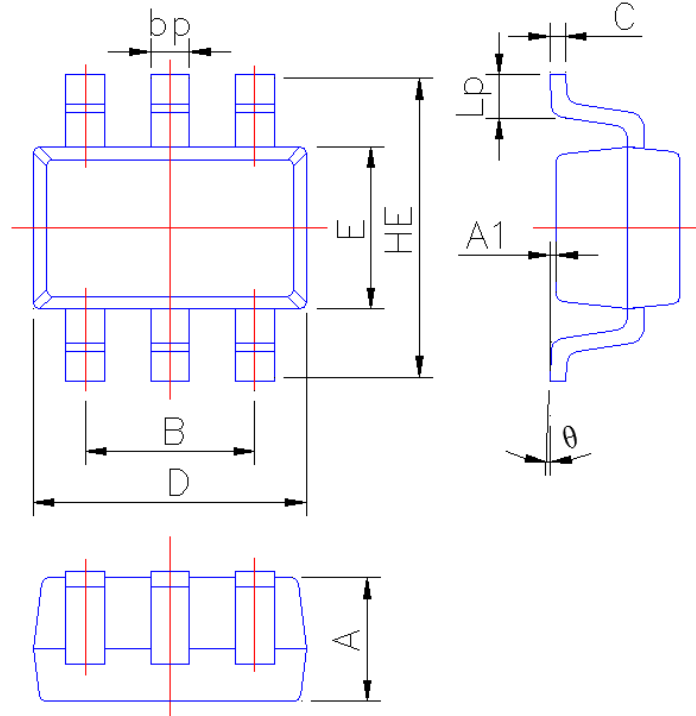
Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current -Continuous	150	mA
P _C	Collector Power Dissipation	150	mW
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =50μA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =50μA, I _C =0	7			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =7V, I _C =0			0.1	μA
DC current gain	h _{FE}	V _{CE} =6V, I _C =1mA	120		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =50mA, I _B =5mA			0.4	V
Transition frequency	f _T	V _{CE} =12V, I _C =2mA, f=100MHz		180		MHz
Collector output capacitance	C _{ob}	V _{CB} =12V, I _E =0, f=1MHz		2.0	3.5	pF

SOT-363-Package Outline Dimensions



Symbol	Dimension in Millimeters	
	Min	Max
A	0.90	1.00
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.45
C	0.09	0.15
D	2.00	2.20
E	1.15	1.35
HE	2.15	2.55
Lp	0.25	0.46
θ	0°	6°